

SANYO Semiconductors DATA SHEET



Bi-CMOS LSI For camera sensor Power supply for charge pump

Overview

The LV5710GP is power supply for charge pump for camera sensor.

Functions

- Regulating the 5V input by boosting it three-fold with the charge pump to the specified voltage.
- Output voltage variable with external resistor.
- Soft start function incorporated, which reduces the rush current at start of charge pump.
- Timer-latch type short-circuit protective function incorporated.

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Maximum supply voltage	V _{DD} max		6.0	V
Allowable power dissipation	Pd max	with specified substrate *	0.55	W
Operating temperature	Topr		-20 to +80	°C
Storage temperature	Tstg		-40 to +125	°C

* : Specified substrate : 114.3mm×76.1mm×1.6mm, glass epoxy board

Allowable Operating Ratings at $Ta = 25^{\circ}C$

Duration	Querra ha a l	Que dition o	Ratings			11-14
Parameter	Symbol	Conditions	min	typ	max	Unit V
Supply voltage	V _{DD}		4.5		5.5	V
Input "H" voltage	VINH	EN pin	1.5		V _{DD}	V
Input "L" voltage	VINL	EN pin	-0.1		0.4	V

- Any and all SANYO Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your SANYO Semiconductor representative nearest you before using any SANYO Semiconductor products described or contained herein in such applications.
- SANYO Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all SANYO Semiconductor products described or contained herein.

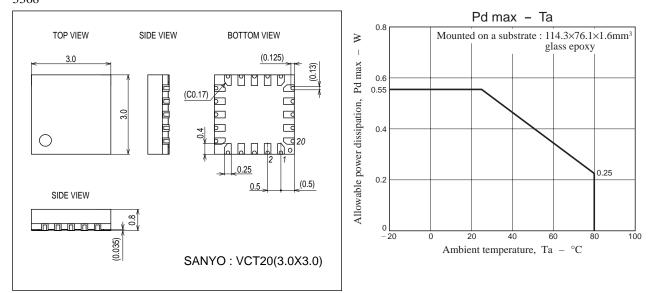
SANYO Semiconductor Co., Ltd. http://semicon.sanyo.com/en/network

LV5710GP

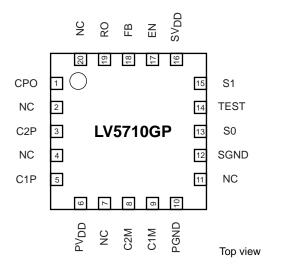
Deveryortex	Querra ha a l		Ratings			
Parameter	Symbol	Conditions	min	typ	Un	
Circuit current drain	I _{DD} 1	EN = L			1	μA
	I _{DD} 2	EN = H No load		12	18	mA
Output load current	I _O ave	IO ave At VOUT = 12V setting			30	mA
Reference voltage	VREF	V _{DD} = 4.5 to 5.5V	1.285	1.305	1.325	V
		Ta = -20°C to +80°C, Design value	1.279		1.331	V
Output voltage at OFF	VOFF	VOFF After capacitive discharge		0	50	mV
Protective circuit masking time	Tmask	Masking time from detection of short-circuit to IC OFF		18	33	ms
Short-circuit protective current	llim		35	50	65	mA
Short-circuit protective voltage	V _{lim}		82.5	87.5	92.5	%
SS end time T _{SSEND}		Time from EN = H to regulator SS OFF Ta = -20°C to +80°C Design value			10	ms
RO load regulation	ΔRO Load 1mA \rightarrow 30mA			30	40	mV
Input pin current	lin	Pins EN	30	40	50	μA
		S0 and S1 pins			1	μA
Power efficiency	Peff CP+regulator			70		%
Rush current Irush No load		No load			300	mA
Oscillation frequency f clk			1.4	1.8	2.3	MHz

Package Dimensions

unit : mm (typ) 3368



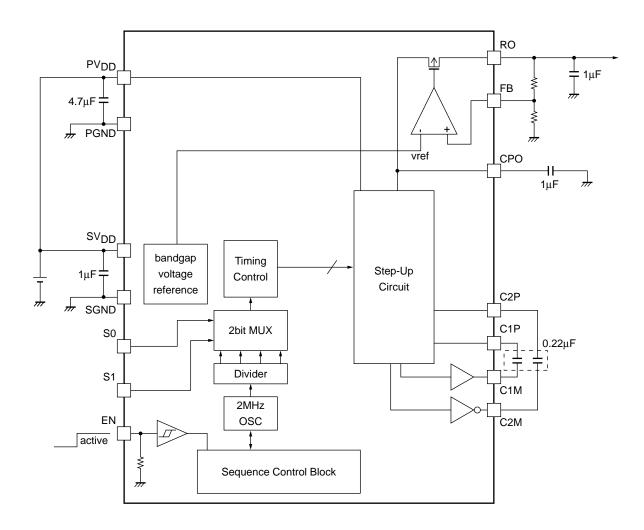
Pin Assignment



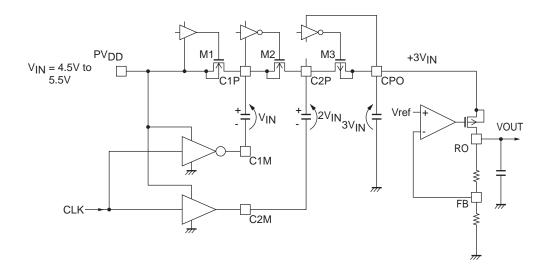
Pin Function

Pin No.	Name	Function
1	CPO	Boost voltage output (6V _{DD} or 5V _{DD})
2	NC	
3	C2P	Boost capacitor connection pin (charge transfer side)
4	NC	
5	C1P	Boost capacitor connection pin (charge transfer side)
6	PVDD	Power system V _{DD} pin
7	NC	
8	C2M	Boost capacitor connection pin (driver side)
9	C1M	Boost capacitor connection pin (driver side)
10	PGND	Power GND pin for the charge pump
11	NC	
12	SGND	Small signal system GND pin
13	SO	Charge pump frequency changeover pin
14	TEST	Test pin (open or short-circuited to GND)
15	S1	Charge pump frequency changeover pin
16	sv _{DD}	Small signal system V _{DD} pin
17	EN	System enable pin (Hi active)
18	FB	Regulator FB pin
19	RO	Regulator output pin
20	NC	

Block Diagram



Equivalent Circuit Diagram

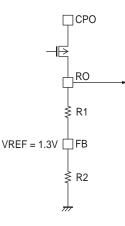


Output Voltage Setting Method

The output voltage of IC-incorporated LDO can be determined as follows :

$$VH = \frac{R1 + R2}{R2} \times VREF$$

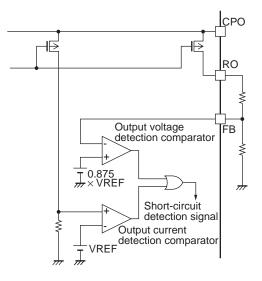
For example, to set the output voltage to 12V, set the resistance Value to $R1 = 1070k\Omega/R2 = 130k\Omega$.



Short-circuit Protective Operation

The RO output pin has the short-circuit protective function.

The over-current detector circuit outputs the detection signal when the output current of 50mA (typ) or more flows or when the output voltage drops below 87.5% (typ). When this detection signal is output continuously for 18ms (typ) or more, IC determines that there is over-current and stops the output. To reset from the stop state, set the EN pin to "L", then set the EN pin to "H" again.



Equivalent circuit of the over-current detection circuit

Selecting the Frequency

According to the logic of S0 and S1, the charge pump operation frequency can be changed. In the case of light load, the reactive power can be reduced by decreasing the operating frequency.

S0	S1	CP operating frequency		
L	L	1MHz		
н	L	500kHz		
L	Н	250kHz		
Н	Н	125kHz		

Startup sequence

	t EN = H after setting DD = 4.5V or more	Stop with EN = L or for over- current protection	Never allow V_{DD} to decrease below 4.5V till EN = L is established
V _{DD}			
EN			
Charge pump output CPO			
Regulator output RO			
SO	Frequency selection Do not allow the sig	nal to change X Frequency selectionX	Do not allow the signal to change X Frequency selection
S1	Frequency selection Do not allow the sig	nal to change X Frequency selection	Do not allow the signal to change X Frequency selection
* CP clock 1MHz			
* CP clock 500kHz			
* CP clock 250kHz			
* CP clock 125kHz			
* IC internal signal	Start at 1MHz Steady o	operation Start at 1MHz	Steady operation
	SS end 10ms (max)		SS end 10ms (max)

EN Pin and VDD

The sequence operation is made at startup. However, startup is not made when the internal circuit has not been reset. To reset the internal circuit, keep the EN pin to "L" till V_{DD} becomes 4.5V or more.

Note that $V_{\mbox{\scriptsize DD}}$ and EN pin cannot be short-circuited for this purpose.

- Specifications of any and all SANYO Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- SANYO Semiconductor Co., Ltd. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all SANYO Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of SANYO Semiconductor Co., Ltd.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the SANYO Semiconductor product that you intend to use.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. SANYO Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

This catalog provides information as of December, 2010. Specifications and information herein are subject to change without notice.